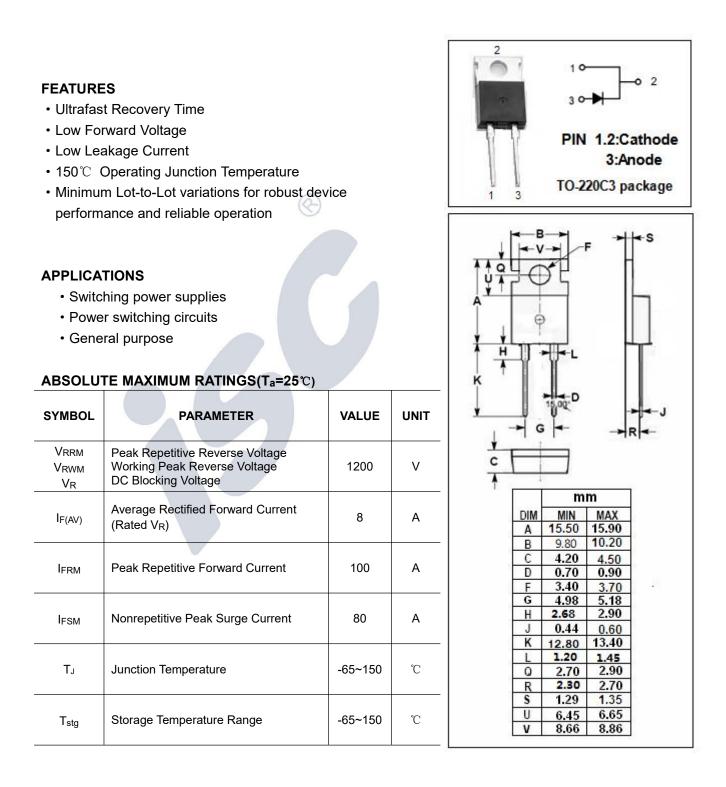


Ultrafast Recovery Rectifier

INCHANGE SEMICONDUCTOR

STTH812D



isc website: <u>www.iscsemi.com</u>

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Ultrafast Recovery Rectifier

STTH812D

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.9	°C/W

ELECTRICAL CHARACTERISTICS(Ta=25°C) (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤2%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
V _{F*}	Maximum Instantaneous Forward Voltage	I _F = 8A	2.2	V
		I⊧= 8A ,Tc=125℃	2.0	
I _R	Maximum Instantaneous Reverse Current	V _{RRM} = 1200V	8	μΑ
		V _{RRM} = 1200V ,Tc=125℃	50	
t _{rr}	Maximum Reverse Recovery Time	I _F =1A I _R =1.0A I _{REC} =0.25A	100	ns

*:Pulse test ,Pulse width=300us,duty cycle≤2%

NOTICE:

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